



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#20/H
3/28/3
Sunder

In re application of

MAHALINGAM NANDAKUMAR

Serial No. 09/252,514 (TI-23103)

Filed February 18, 1999

For: DUAL-COUNTERDOPED CHANNEL FIELD EFFECT TRANSISTOR AND METHOD

Art Unit 2811

Examiner S. Crane

Commissioner for Patents
Washington, D. C. 20231

Sir:

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AMENDMENT UNDER 37 C.F.R. 1.111

In response to the Office action dated February 26, 2003, please amend the above identified application as follows:

In the specification:

Cancel the paragraph on page 6, lines 22 to 34 and replace by amendment as follows:

"Referring to FIGURE 1E, n-type source/drain regions 34 are formed using ion implantation. In this example, source/drain pockets 32 are implanted with an n-type material such as arsenic.. Although source/drain pockets 32 are shown extending around source/drain regions 34 and adjoining isolation trenches 20, it will be understood that source/drain pockets 32 may extend only along the inside portion of source/drain regions 34 adjoining the channel 24. Alternatively, a deeper source/drain implant may be performed to extend source/drain regions 34